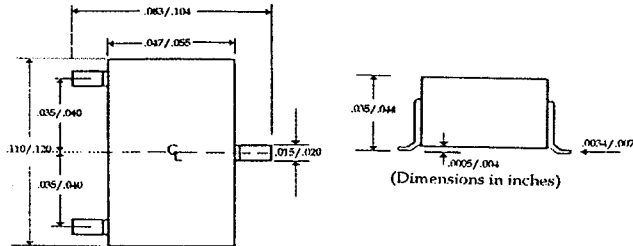
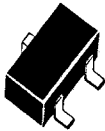




Description
SOT-23

Mechanical Dimensions



N CHANNEL TRANSISTOR

Absolute Maximum Ratings

Drain-Source Voltage.....	60 V
Drain-Gate Voltage (RGS=1MΩ)	60 V
Gate-Source Voltage	+/-40 V
Continuous Drain Current (Ta=25°C)(1)	200 mA
Continuous Drain Current (Ta=100°C)(1)	115 mA
Pulsed Drain Current (Ta=25°C)(2).....	800 mA
Total Power Dissipation (Tc=25°C).....	200 mW
Derate above 25°C	0.16 Mw / °C
Storage Temperature.....	-55 to 150 °C
Operating Junction Temperature	-55 to 150 °C
Lead Temperature, for 10 second Soldering.....	260 °C

Thermal Characteristics

Thermal Resistance, Junction-to-Ambient 625 °C / W

Characteristics (Ta=25°C)

Parameter	Symbol	Test Conditions	Min	Typ.	Max	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0, I _D =10uA	60	-	-	V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =2.5V, I _D =0.25mA	1	-	2.5	V
Gate Source Leakage Current, Forward	I _{GSS/F}	V _{GS} =+20V, V _{DS} =0	-	-	100	nA
Gate Source leakage Current, Reverse	I _{GSS/R}	V _{GS} =-20V, V _{DS} =0	-	-	100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V, V _{GS} =0	-	-	1	uA
On-State Drain Current	I _{D(ON)}	V _{DS} >2V _{DS(ON)} , V _{GS} =10V	500	-	-	mA
Static Drain-Source On-State Voltage	V _{DS(ON)}	I _D =50mA, V _{GS} =5V	-	-	0.375	V
		I _D =500mA, V _{GS} =10V	-	-	3.75	V
Static Drain-Source On-State Resistance	R _{DS(ON)}	I _D =50mA, V _{GS} =5V	-	-	7.5	Ω
		I _D =500mA, V _{GS} =10V	-	-	7.5	Ω
Forward Transconductance	G _{FS}	V _{DS} >2V _{DS(ON)} , I _D =200mA	80	-	-	mS
Input Capacitance	C _{iss}	V _{DS} =25V, V _{GS} =0, f=1MHz	-	-	50	pF
Output Capacitance	C _{oss}		-	-	25	pF
Reverse Transfer Capacitance	C _{rss}		-	-	5	pF

(1)The Power Dissipation of the package may result in a continuous drain current.
 (2)Pulse Width≤300us, Duty cycle≥2%.

